
2SK1623(L), 2SK1623(S)

Silicon N-Channel MOS FET

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Application

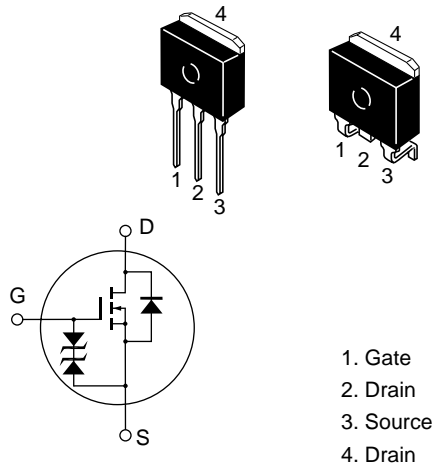
High speed power switching

Features

- Low on-resistance
- High speed switching
- 4 V gate drive device
 - Can be driven from 5 V source
- Suitable for motor drive, DC-DC converter, power switch and solenoid drive

Outline

LDDPAK



2SK1623(L), 2SK1623(S)

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{(BR)DSS}$	100	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	20	A
Drain peak current	$I_{D(pulse)}^{*1}$	80	A
Body to drain diode reverse drain current	I_{DR}	20	A
Channel dissipation	P_{ch}^{*2}	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

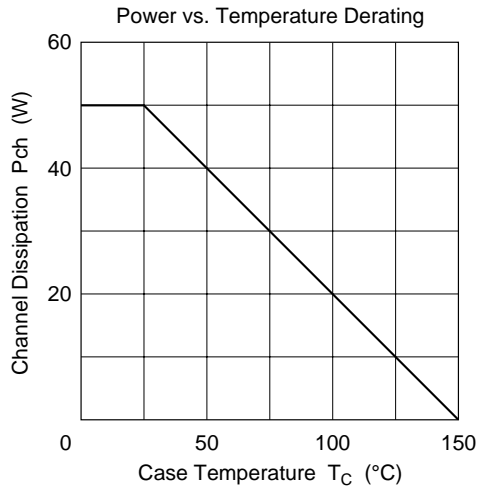
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

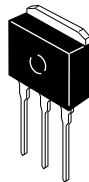
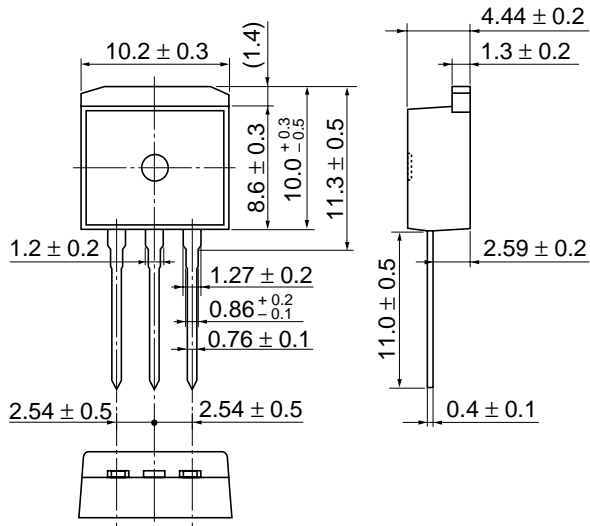
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	100	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	250	μA	$V_{DS} = 80 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static Drain to source on state resistance	$R_{DS(on)}$	—	0.065	0.085	Ω	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
		—	0.085	0.12	Ω	$I_D = 10 \text{ A}, V_{GS} = 4 \text{ V}^{*1}$
Forward transfer admittance	$ y_{fs} $	10	16	—	S	$I_D = 10 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	C_{iss}	—	1300	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	C_{oss}	—	540	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance	C_{rss}	—	160	—	pF	
Turn-on delay time	$t_{d(on)}$	—	12	—	ns	$I_D = 10 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time	t_r	—	100	—	ns	$R_L = 3 \text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	—	300	—	ns	
Fall time	t_f	—	150	—	ns	
Body to drain diode forward voltage	V_{DF}	—	1.3	—	V	$I_F = 20 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	300	—	ns	$I_F = 20 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A}/\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SK1302.





Hitachi Code	LPAK (L)
JEDEC	—
EIAJ	—
Weight (reference value)	1.4 g

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